

<p>Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <small>(use as many sheets as necessary)</small></p>		<p>Complete if Known</p> <table border="1" style="width: 100%; border-collapse: collapse;"> <tr> <td style="width: 30%;">Application Number</td> <td colspan="4">09/945554</td> </tr> <tr> <td>Filing Date</td> <td colspan="4">August 30, 2001</td> </tr> <tr> <td>First Named Inventor</td> <td colspan="4">Forbes, Leonard</td> </tr> <tr> <td>Group Art Unit</td> <td colspan="4">2826</td> </tr> <tr> <td>Examiner Name</td> <td colspan="4">Dickey, Thomas</td> </tr> </table>					Application Number	09/945554				Filing Date	August 30, 2001				First Named Inventor	Forbes, Leonard				Group Art Unit	2826				Examiner Name	Dickey, Thomas			
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		<p>Attorney Docket No: 1303.028U\$1</p>																													
<p>Sheet 1 of 2</p>																															

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Examiner Initials*	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS						
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.				T*
TB		AARIK, JAAN , et al., "Anomalous effect of temperature on atomic layer deposition of titanium oxide", <u>Journal of Crystal Growth</u> , (2000),pp. 531-537				
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		Examiner Name	Dickey, Thomas
Attorney Docket No: 1303.028US1			

TJ		SMITH, RYAN C., et al., "Chemical vapour deposition of the oxides of titanium, zirconium and hafnium for use as high-k materials in microelectronic devices. A carbon-free precursor for the synthesis of hafnium dioxide", <u>Advanced Materials for Optics and Electronics</u> , (2000), 2 pages	
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Substitute Disclosure Statement Form (PTO-1449)

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached